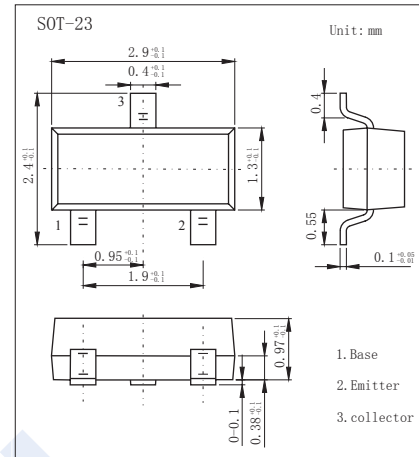


PNP Transistors

2SA1617

■ Features

- Collector Current Capability $I_C = -100\text{mA}$
- Collector Emitter Voltage $V_{CE0} = -50\text{V}$



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-55	V
Collector - Emitter Voltage	V_{CE0}	-50	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_C	-100	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_J	150	°C
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -100\ \mu\text{A}$, $I_E = 0$	-55			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -1\ \text{mA}$, $I_B = 0$	-50			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100\ \mu\text{A}$, $I_C = 0$	-5			
Collector-base cut-off current	I_{CB0}	$V_{CB} = -30\ \text{V}$, $I_E = 0$			-0.1	uA
Emitter cut-off current	I_{EB0}	$V_{EB} = -5\ \text{V}$, $I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10\ \text{mA}$, $I_B = -1\ \text{mA}$			-0.2	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -10\ \text{mA}$, $I_B = -1\ \text{mA}$			-1.2	
Base - emitter voltage	V_{BE}	$V_{CE} = -12\ \text{V}$, $I_C = -2\ \text{mA}$			-0.8	
DC current gain	h_{FE}	$V_{CE} = -12\ \text{V}$, $I_C = -2\ \text{mA}$	100		320	

■ Classification of h_{FE}

Type	2SA1617-B	2SA1617-C
Range	100-200	160-320
Marking	VIB	VIC